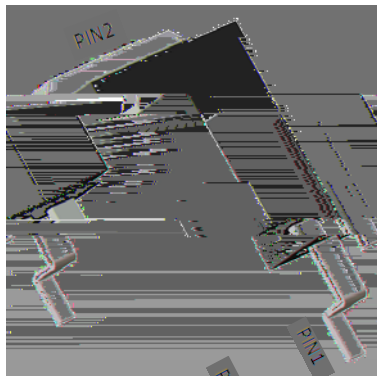


- Adopt FRED chip
- Low forward Voltage drop
- Fast reverse recovery time
- High frequency operation
- High purity, high temperature epoxy encapsulation for enhanced mechanical strength and moisture resistance
- Guard ring for enhanced ruggedness and long term reliability

Typical applications are in switching power supplies, converters, freewheeling diodes, and reverse battery protection.

- : TO-263
Molding compound meets UL 94 V-0 flammability rating, RoHS-compliant
- : Tin plated leads, solderable per J-STD-002 and JESD22-B102
- : As marked

■ (T_j=25 Unless otherwise specified)

Device marking code			MURB1060CT
Repetitive Peak Reverse Voltage	V _{RRM}	V	600
Average Rectified Output Current @60Hz sine wave, R-load, T _c (FIG.1)	I _O	A	10
Surge(Non-repetitive)Forward Current @60Hz half sine-wave, 1 cycle, T _j =25	I _{FSM}	A	50
Current Squared Time @1ms≤t≤8.3ms T _j =25	I ² t	A ² s	10
Storage Temperature	T _{stg}		-55 ~ +175
Junction Temperature	T _j		-55 ~ +175
Typical Junction capacitance @4V,1MHz	C _j	pF	20



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Instantaneous forward voltage drop per diode	V_{FM}	V	$I_{FM}=5.0A$ @ $T_J=25$		-	1.45
			$I_{FM}=5.0A$ @ $T_J=150$			1.3
DC reverse current at rated DC blocking voltage per diode	I_{RRM1}	uA	$V_{RM}=V_{RRM}$ $T_J=25$		-	5.0
	I_{RRM2}		$V_{RM}=V_{RRM}$ $T_J=150$		-	35
Reverse Recovery Time	T_{rr}	ns	$I_F=0.5A$ $I_{RM}=1A$ $I_{RR}=0.25A$ $T_J=25$		-	25
			$T_J=25$	$I_F=5A$ $di/dt=-200A/us$ $V_{RM}=200V$	-	50.8
			$T_J=125$		-	81.8
Peak recovery current	I_{RRM}	A	$T_J=25$		-	3.06
			$T_J=125$		-	5.07
Reverse recovery charge	Q_{rr}	nC	$T_J=25$		-	78.88
			$T_J=125$		-	280

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$T_J=25$ Unless otherwise specified

Thermal Resistance	Between junction and case	$R_{\theta J-C}$	$/W$	2.0
Thermal Resistance	Between junction and Air	$R_{\theta J-A}$	$/W$	50

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(Example)

MURB1060CT	Approximate 1.43	800	/	8000	13 ° Reel



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